DATA SHEET

MOS FIELD EFFECT TRANSISTOR $\mu PA2510$

PACKAGE DRAWING (Unit: mm)

P-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

TYP.

DESCRIPTION

NEC

The μ PA2510, which has a heat spreader, is P-channel MOS Field Effect Transistor designed for power management applications of notebook computers.

FEATURES

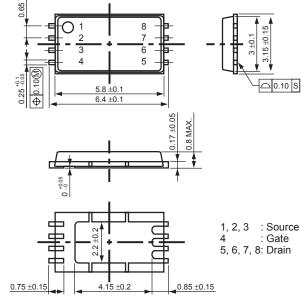
- *μ* PA2510 has a thin surface mount package with a heat spreader. The land size is same as 8-pin TSSOP.
- Low on-state resistance $R_{DS(on)1} = 10.1 \text{ m}\Omega \text{ MAX.}$ (V_{GS} = -10.0 V, I_D = -9.0 A) $R_{DS(on)2} = 14.0 \text{ m}\Omega \text{ MAX.}$ (V_{GS} = -4.5 V, I_D = -9.0 A)
- Low Ciss: 3000 pF TYP. (VDs = -10.0 V, VGs = 0 V)

ORDERING INFORMATION

PART NUMBER	PACKAGE
μ PA2510TM	8PIN HWSON

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vgs = 0 V)	VDSS	-30.0
Gate to Source Voltage (VDS = 0 V)	Vgss	∓20.0
Drain Current (DC) ^{Note1}	D(DC)	∓18.0
Drain Current (pulse) Note2	D(pulse)	∓72.0
Total Power Dissipation Note1	Ρτ	2.7
Channel Temperature	Tch	150
Storage Temperature	Tstg	–55 to +150
Single Avalanche Current Note3	las	-18.0
Single Avalanche Energy Note3	Eas	32.4



V V A

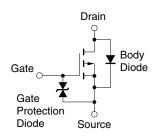
A W

°C °C

А

m.J

EQUIVALENT CIRCUIT



Notes 1. Mounted on FR-4 board of 25 cm² x 1.6 mm, PW \leq 10 sec

- **2.** PW \leq 10 μ s, Duty Cycle \leq 1%
- 3. Starting T_{ch} = 25°C, V_{DD} = -30 V, R_G = 25 Ω , V_{GS} = $-20.0 \rightarrow 0$ V

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding

the rated voltage may be applied to this device.

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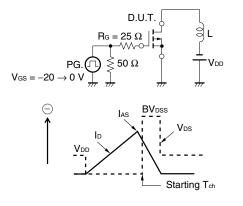
ELECTRICAL CHARACTERISTICS (TA = 25°C)

			1		-	
	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = -30.0 V, V _{GS} = 0 V			-1.0	μA
Gate Leakage Current	lgss	V _{GS} = ∓20.0 V, V _{DS} = 0 V			∓10.0	μA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = -10.0 V, I _D = -1.0 mA	-1.0		-2.5	V
Forward Transfer Admittance Note	y fs	V _{DS} = -10.0 V, I _D = -9.0 A	12			S
Drain to Source On-state Resistance Note	RDS(on)1	V_{GS} = -10.0 V, I _D = -9.0 A		7.5	10.1	mΩ
	RDS(on)2	V_{GS} = -4.5 V, I _D = -9.0 A		9.5	14.0	mΩ
Input Capacitance	Ciss	V _{DS} = -10.0 V		3000		pF
Output Capacitance	Coss	V _{GS} = 0 V		940		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		500		pF
Turn-on Delay Time	td(on)	V _{DD} = -15.0 V, I _D = -9.0 A		12		ns
Rise Time	tr	V _{GS} = -10.0 V		18		ns
Turn-off Delay Time	td(off)	R _G = 10 Ω		270		ns
Fall Time	tr			170		ns
Total Gate Charge	QG	V _{DD} = -24.0 V		70		nC
Gate to Source Charge	Q _{GS}	V _{GS} = -10.0 V		8		nC
Gate to Drain Charge	Qgd	I _D = -18.0 A		22		nC
Body Diode Forward Voltage Note	VF(S-D)	I⊧ = 18.0 A, V _{GS} = 0 V		0.85		V
Reverse Recovery Time	trr	I⊧ = 18.0 A, V _{GS} = 0 V		80		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/µs		68		nC

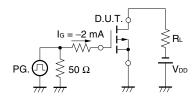
Note Pulsed: PW \leq 350 μ s, Duty Cycle \leq 2%

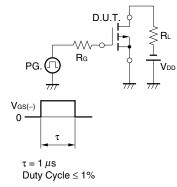
TEST CIRCUIT 1 AVALANCHE CAPABILITY

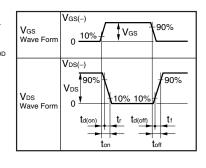
TEST CIRCUIT 2 SWITCHING TIME



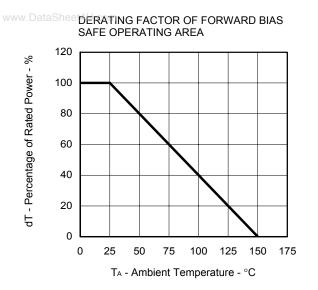
TEST CIRCUIT 3 GATE CHARGE

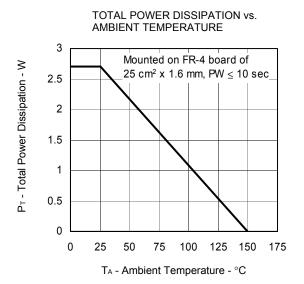




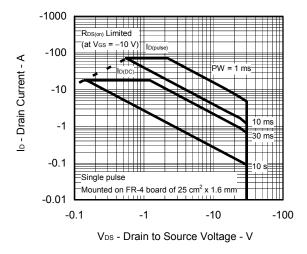


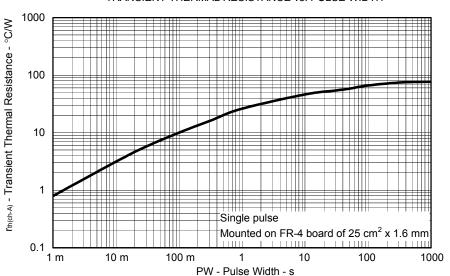
TYPICAL CHARACTERISTICS (T_A = 25°C)





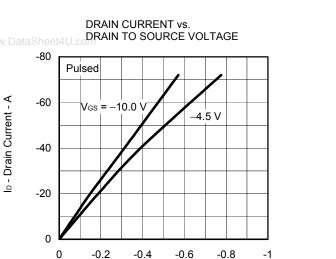
FORWARD BIAS SAFE OPERATING AREA





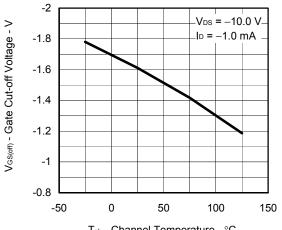
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

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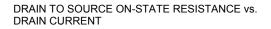


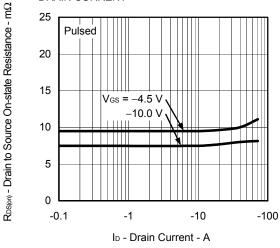
V_{DS} - Drain to Source Voltage - V



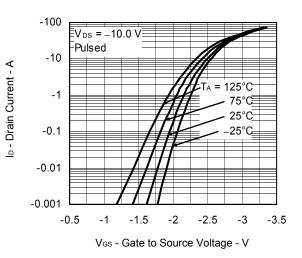


T_{ch} - Channel Temperature - °C

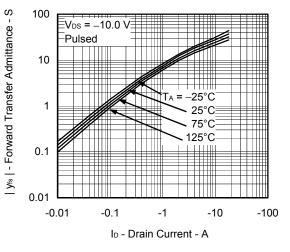




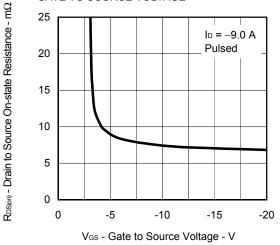
FORWARD TRANSFER CHARACTERISTICS



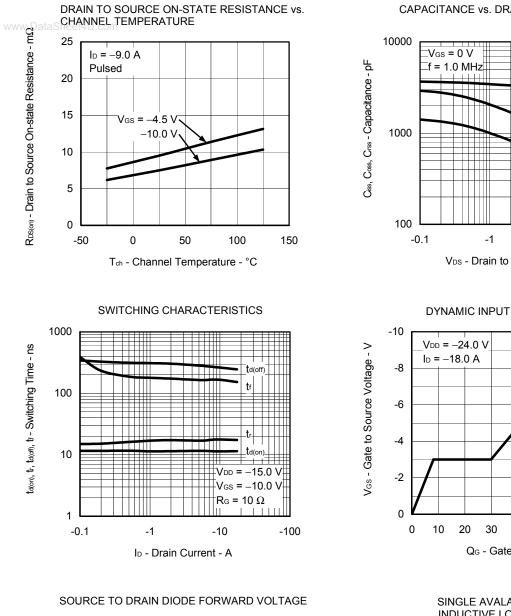
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

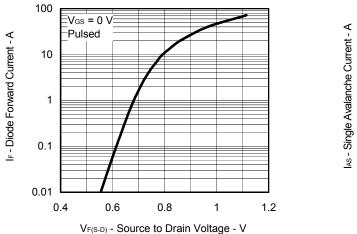


DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

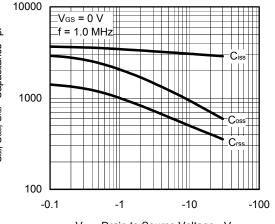


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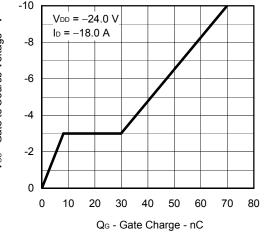


CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

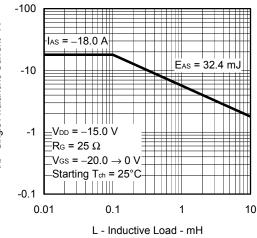


VDS - Drain to Source Voltage - V

DYNAMIC INPUT CHARACTERISTICS

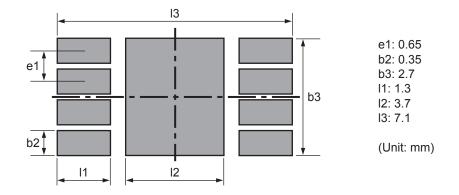






EXAMPLE OF THE LAND PATTERN

Please optimize the land pattern in consideration of density, appearance of solder fillets, common difference, etc in an actual design.



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